

**Silicon NPN transistor triple diffused type
CP020**

[Applications]

High voltage

[Feature]

High voltage V_{CEO}= 350V, V_{CBO}= 400V

[Absolute maximum ratings (Ta=25C)]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	V _{CBO}	400	V
Collector-emitter voltage	V _{CEO}	350	V
Emitter-base voltage	V _{EBO}	7	V
Collector current	I _C	100	mA
Junction temperature	T _j	125	C
Storage temperature	T _{stg}	-55 to 125	C

[Electrical characteristics (Ta=25C)]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	B _V C _B O	400	-	-	V	I _C = 50uA, I _E = 0A
Collector-emitter breakdown voltage	B _V C _E O	350	-	-	V	I _C = 10mA, I _B = 0A
Emitter-base breakdown voltage	B _V E _B O	7	-	-	V	I _E = 50uA, I _C = 0A
Collector cutoff current	I _C B _O	-	-	10	uA	V _{CB} = 300V
DC current gain	h _{FE}	30	-	333	-	V _{CE} = 10V, I _C = 10mA
Collector-emitter saturation voltage	V _{CE} (sat)	-	-	0.5	V	I _C = 10mA, I _B = 1mA

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.

